Docket No.: OGOSH53USA

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No. : 10/595,660 Confirmation No. 4264

Applicant : Yuichiro Shindo

371 Filed : May 3, 2006

Art Unit : 1793

Examiner : Jessee Randall Roe

Customer No. : 00270

Title : HIGH PURITY HAFNIUM, TARGET AND THIN FILM

COMPRISING SAID HIGH PURITY HAFNIUM, AND METHOD FOR PRODUCING HIGH PURITY HAFNIUM

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

RESPONSE TO RESTRICTION REQUIREMENT

Sir:

This is a timely response to the written Restriction Requirement dated July 1, 2008.

Election

In the present application, Applicants elect without traverse to prosecute the invention directed to hafnium having a purity of 4N or higher. Thus, <u>Group I</u> is elected and includes claims 1 and 2.

Please charge any deficiency or credit any overpayment for entering this Response to our deposit account no. 08-3040.

Respectfully submitted, HOWSON & HOWSON LLP Attorneys for Applicant

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